



November 18, 2003

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

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Subject:	Serial No. 10/647,716 08/25/03
	Tai Min et al.

MAGNETIC RANDOM ACCESS MEMORY  
DESIGNS WITH CONTROLLED MAGNETIC  
SWITCHING MECHANISM

Grp. Art Unit:	-----
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#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on November 21, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 11/21/03

U.S. Patent 6,242,770 to Bronner et al., "Diode Connected to a Magnetic Tunnel Junction and Self Aligned with a Metallic Conductor and Method for Forming the Same," teaches a method for forming thin film conductors as word and bit lines so that the MTJ device is in close proximity to a lower line and a diode is located below that line.

U.S. Patent 5,757,695 to Shi et al., "MRAM with Aligned Magnetic Vectors," teaches the formation of an ellipsoidal MTJ cell wherein the magnetization vectors are aligned along the length (major axis) of the cell and which do not present variously oriented edge domains, high fields and poles at the ends of the element.

U.S. Patent 6,205,053 to Anthony, "Magnetically Stable Magnetoresistive Memory Element," teaches the formation of an MTJ device having first and second layers which are substantially "H" and "I" shaped.

U.S. Patent 6,005,800 to Koch et al., "Magnetic Memory Array with Paired Asymmetric Memory Cells for Improved Write Margin," teaches the formation of cells with two shapes, which are mirror images of each other.

HT-02-014

U.S. Patent Application HT-02-015, Serial No. 10/650,600, filed 08/28/03, assigned to the same assignee as the current invention, discusses the use of magnetic tunnel junctions (MTJ) as storage elements (cells) in non-volatile memory cell arrays, called magnetic random access memories (MRAM).

Sincerely,



Stephen B. Ackerman,  
Reg. No. 37761

## INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several shovels if necessary)

Doctor Number (Optional)

HT-02-014

American Names

101647,716

Jiayi Min et al.

Filing Date / - / Group Art Unit

Filing Date 08/25/03

**U. S. PATENT DOCUMENTS**



## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Portion or Pages, Etc.)

U.S. Patent Application HT-02-015, Serial No. 10/650,600,  
filed 08/28/03, assigned to the same assignee.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.